ON Semiconductor®

December 2017

FFB2222A / FMB2222A / MMPQ2222A
NPN Multi-Chip General-Purpose Amplifier

Description

This device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from process 19.

Block Diagram

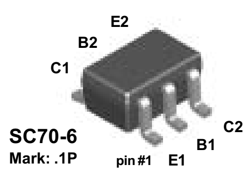

Figure 1. FFB2222A Device Package

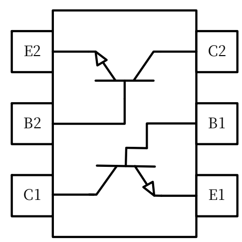

Figure 2. FFB2222A Internal Connection

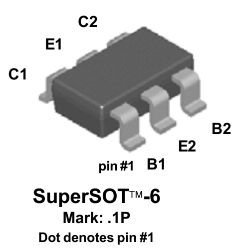

Figure 3. FMB2222A Device Package

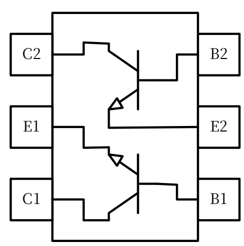

Figure 4. FMB2222A Internal Connection

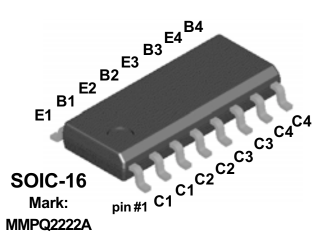

Figure 5. MMPQ2222A Device Package

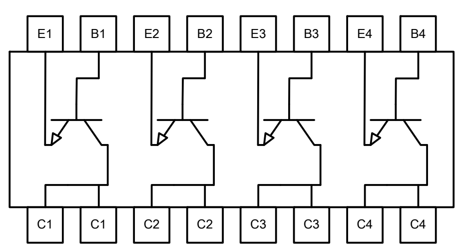

Figure 6. MMPQ2222A Internal Connection

Ordering Information

Part Number	Top Mark	Package	Packing Method
FFB2222A	.1P	SC70 6L	Tape and Reel
FMB2222A	.1P	SSOT 6L	Tape and Reel
MMPQ2222A	MMPQ2222A	SOIC 16L	Tape and Reel

Absolute Maximum Ratings(1)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	45	V
V_{CBO}	Collector-Base Voltage	75	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Note:

1. These ratings are based on a maximum junction temperature of 150°C. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty cycle operations.

Thermal Characteristics(2)

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Max.			Unit
		FFB2222A	FMB2222A	MMPQ2222A	
P_D	Total Device Dissipation	300	700	1,000	mW
	Derate Above 25°C	2.4	5.6	8.0	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	415	180		°C/W
	Thermal Resistance, Junction-to-Ambient, Effective 4 Dies			125	
	Thermal Resistance, Junction-to-Ambient, Each Die			240	

Note:

2. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage[3]	I_C = 10 mA, I_B = 0	40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 10 µA, I_E = 0	75			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 10 µA, I_C = 0	5.0			V
I_{CBO}	Collector Cut-Off Current	V_{CB} = 60 V, I_E = 0			10	nA
I_{EBO}	Emitter Cut-Off Current	V_{EB} = 3.0 V, I_C = 0			10	nA
h_{FE}	DC Current Gain	I_C = 0.1 mA, V_{CE} = 10 V	35			
		I_C = 1.0 mA, V_{CE} = 10 V	50			
		I_C = 10 mA, V_{CE} = 10 V	75			
		I_C = 150 mA, V_{CE} = 10 V[3]	100		300	
		I_C = 150 mA, V_{CE} = 1.0 V[3]	50			
		I_C = 500 mA, V_{CE} = 10 V[3]	40			
$V_{CE}(sat)$	Collector-Emitter Saturation Voltage[3]	I_C = 150 mA, I_B = 15 mA			0.3	V
		I_C = 500 mA, I_B = 50 mA			1.0	
$V_{BE}(sat)$	Base-Emitter Saturation Voltage[3]	I_C = 150 mA, I_B = 15 mA			1.2	V
		I_C = 500 mA, I_B = 50 mA			2.0	
f_T	Current Gain - Bandwidth Product	I_C = 20 mA, V_{CE} = 20 V, f = 100 MHz		300		MHz
C_{obo}	Output Capacitance	V_{CB} = 10 V, I_E = 0, f = 100 kHz		4.0		pF
C_{ibo}	Input Capacitance	V_{EB} = 0.5 V, I_C = 0, f = 100 kHz		20		pF
NF	Noise Figure	I_C = 100 µA, V_{CE} = 10 V, R_S = 1.0 kΩ, f = 1.0 kHz		2.0		dB
t_d	Delay Time	V_{CC} = 30 V, $V_{BE(OFF)}$ = 0.5 V, I_C = 150 mA, I_{B1} = 15 mA		8		ns
t_r	Rise Time			20		ns
t_s	Storage Time	V_{CC} = 30 V, I_C = 150 mA, I_{B1} = I_{B2} = 15 mA		180		ns
t_f	Fall Time			40		ns

Note:

3. Pulse test: pulse width ≤ 300 µs, duty cycle ≤ 2.0%.

Typical Performance Characteristics

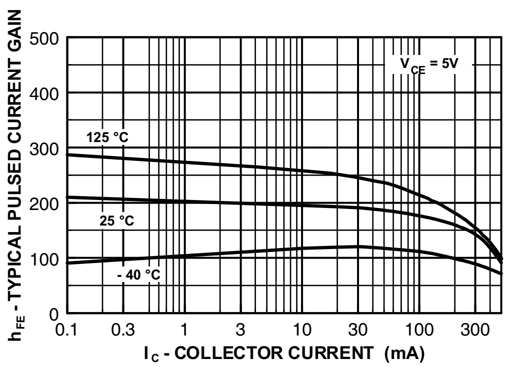

Figure 7. Typical Pulsed Current Gain vs. Collector Current

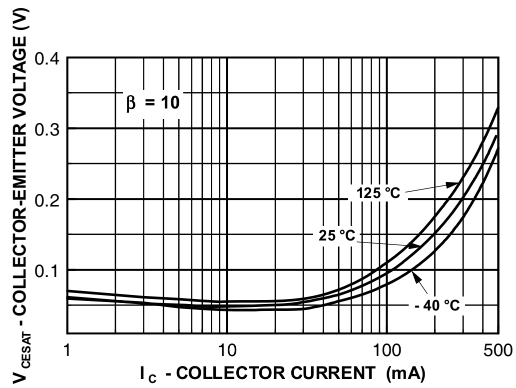

Figure 8. Collector-Emitter Saturation Voltage vs. Collector Current

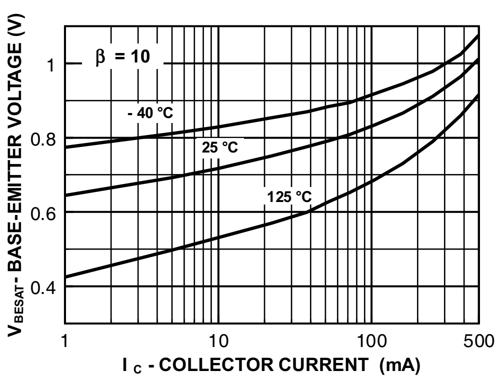

Figure 9. Base-Emitter Saturation Voltage vs. Collector Current

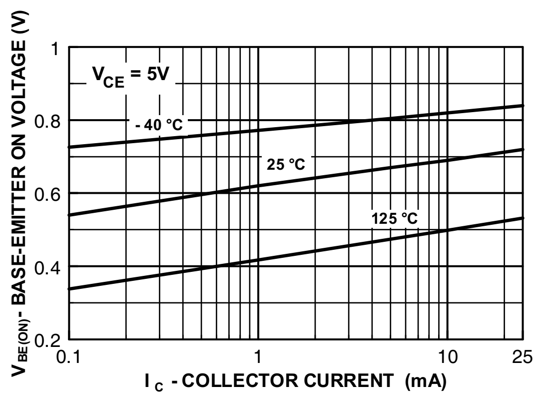

Figure 10. Base-Emitter On Voltage vs. Collector Current

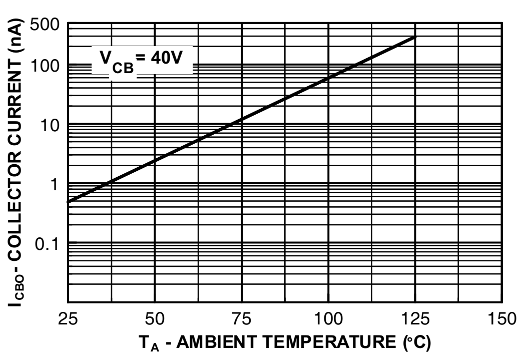

Figure 11. Collector Cut-Off Current vs. Ambient Temperature

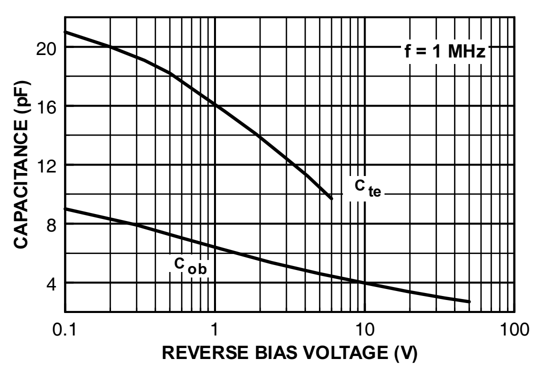

Figure 12. Emitter Transition and Output Capacitance vs. Reverse Bias Voltage

Typical Performance Characteristics (Continued)

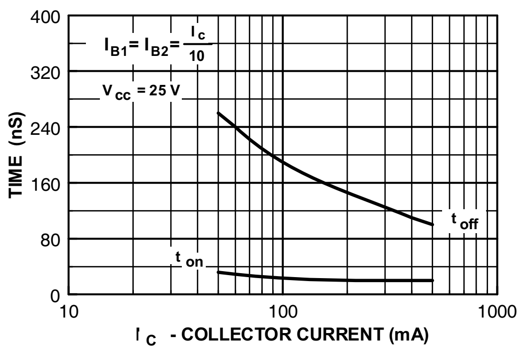

Figure 13. Turn-On and Turn-Off Times vs. Collector Current

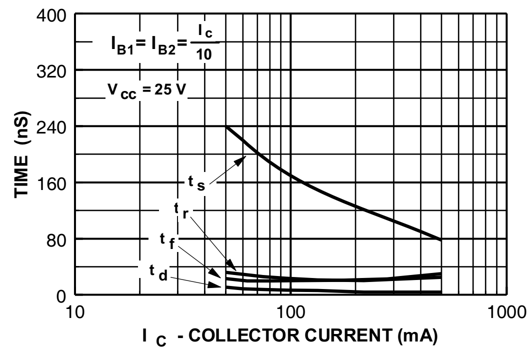

Figure 14. Switching Time vs. Collector Current

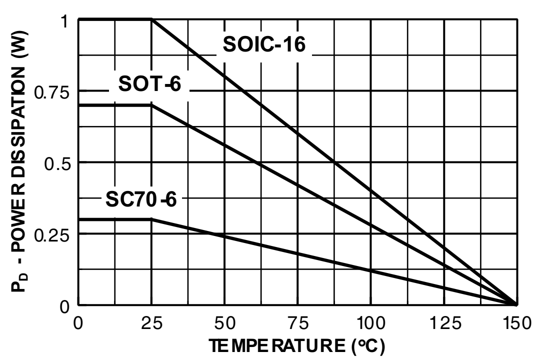

Figure 15. Power Dissipation vs. Ambient Temperature

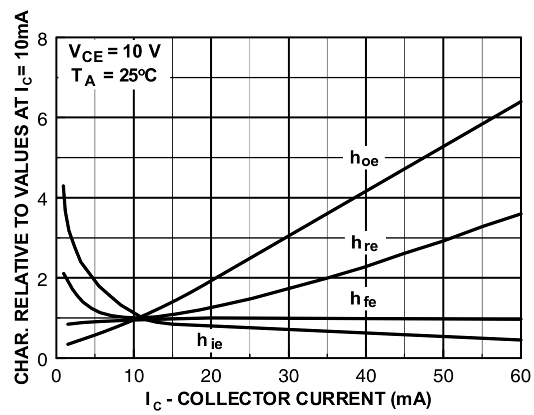

Figure 16. Common Emitter Characteristics

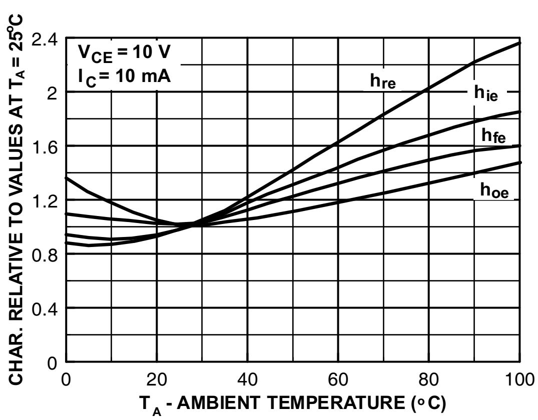

Figure 17. Common Emitter Characteristics

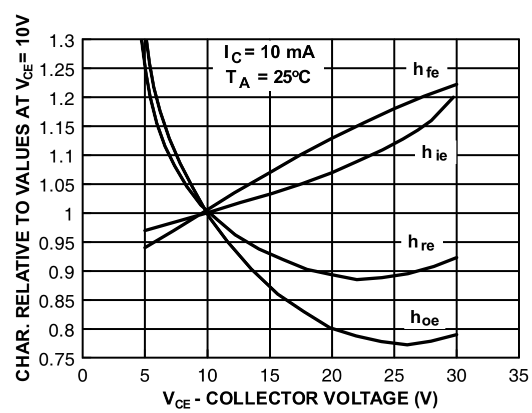

Figure 18. Common Emitter Characteristics

Test Circuits

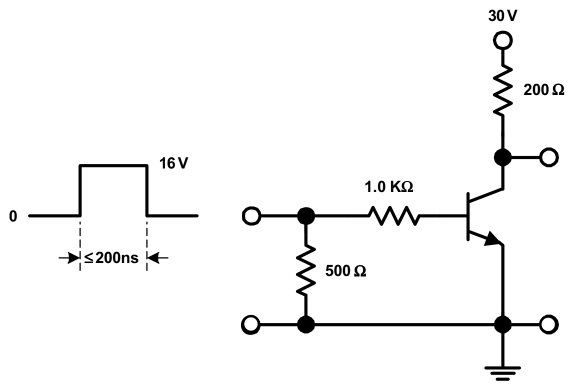

Figure 19. Saturated Turn-On Switching Time

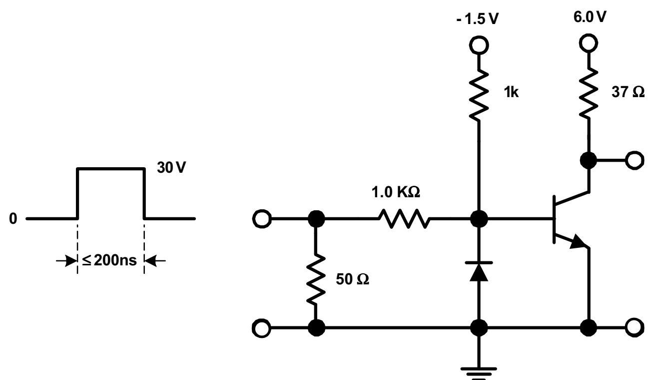

Figure 20. Saturated Turn-Off Switching Time

Physical Dimensions

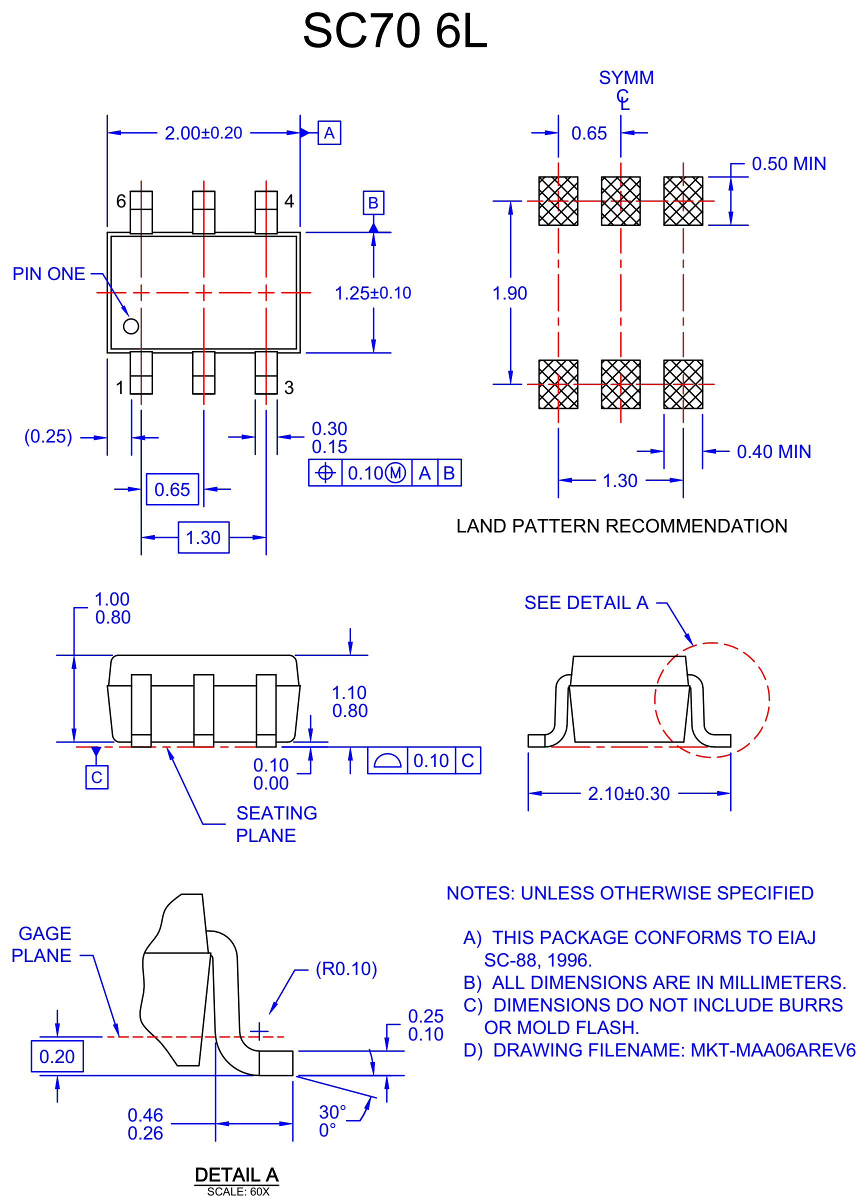

Figure 25. 6-LEAD, SC70, EIAJ SC-88, 1.25 MM WIDE (ACTIVE)

Physical Dimensions (Continued)

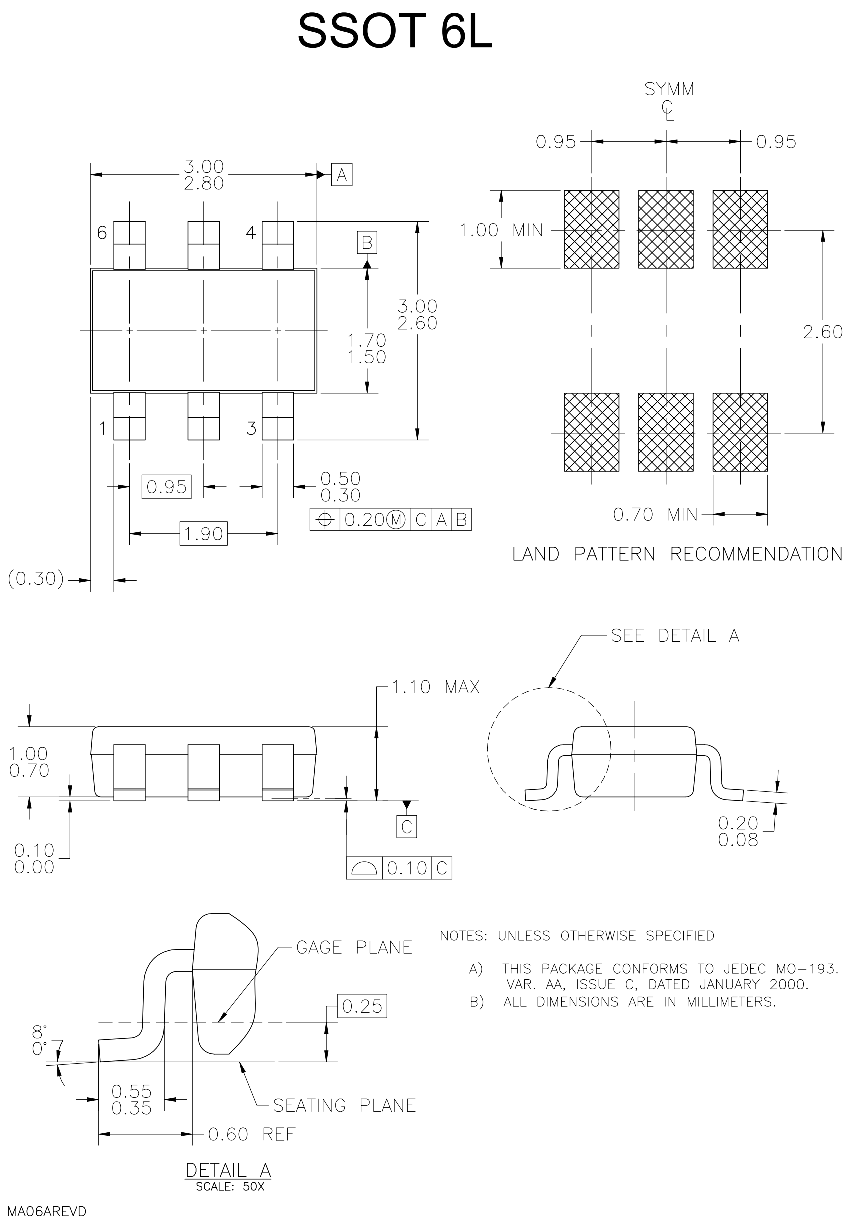

Figure 26. 6-LEAD, SUPERSOT-6, JEDEC MO-193, 1.6 MM WIDE (ACTIVE)

Physical Dimensions (Continued)

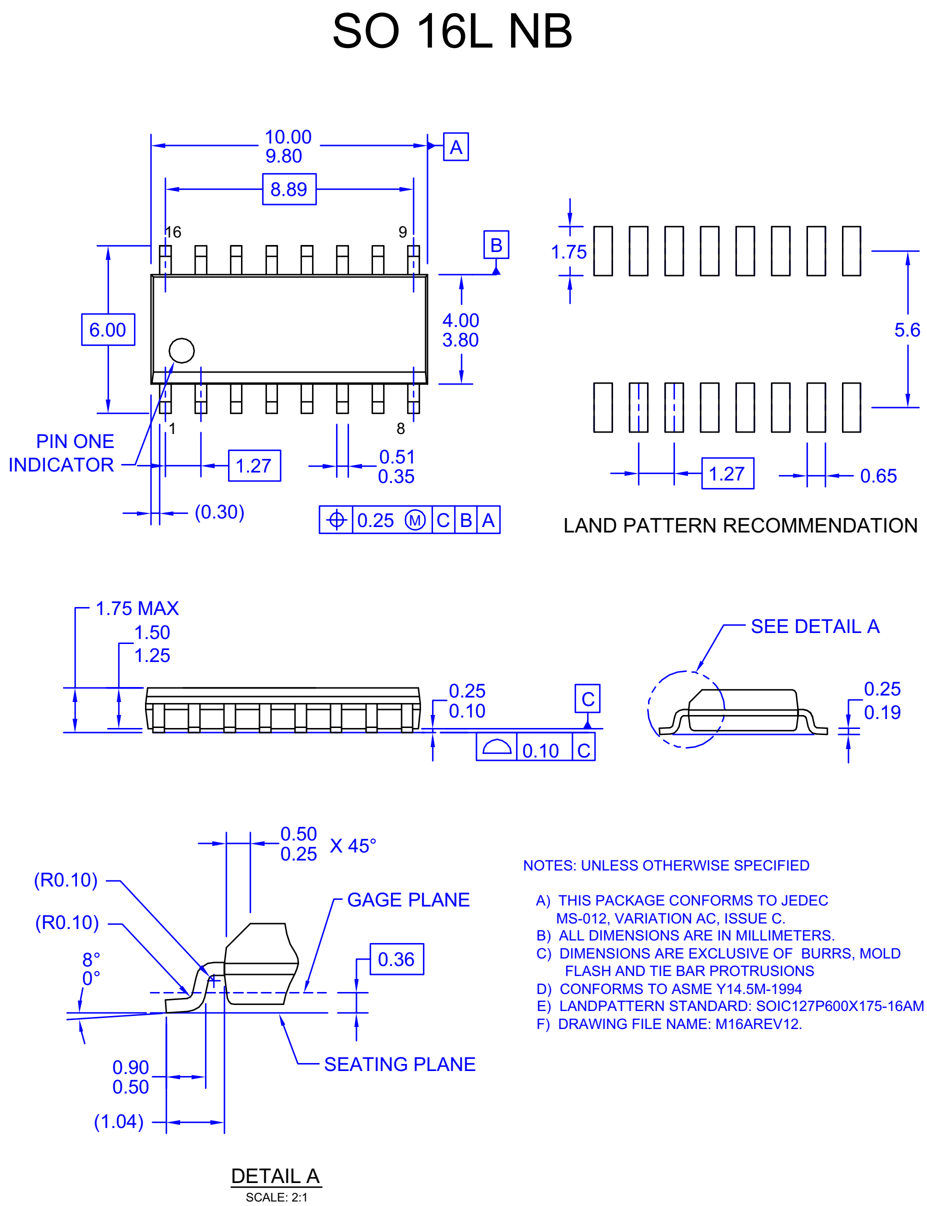

Figure 27. 16-LEAD, SOIC, JEDEC MS-012, 0.150 inch, NARROW BODY (ACTIVE)

PUBLICATION ORDERING INFORMATION

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